

Practitioner's Docket No.: 811_107

**AFTER FINAL
PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Makoto IWAI, Katsuhiro IMAI and Minoru IMAEDA

Serial No.: 10/594,846

Group Art Unit: 1714

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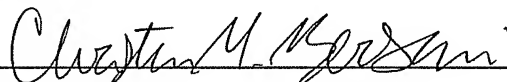
Conf. No.: 3664

For: GALLIUM NITRIDE SINGLE CRYSTAL GROWING METHOD
AND GALLIUM NITRIDE SINGLE CRYSTAL

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

**CERTIFICATION OF EFS
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I hereby certify that this paper is being transmitted via EFS to the Patent and Trademark Office on October 22, 2010.


Christina M. Bersani

AMENDMENT AFTER FINAL REJECTION*

Sir:

In response to the Office Action mailed July 22, 2010, please amend the above-identified application as follows:

Amendments to the Claims begin on page 2 of this paper.

Remarks/Arguments begin on page 4 of this paper.

* An RCE is filed herewith.